

INFORMATION DISCLOSURE CITATION
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FIS9-2001-0 295-US2

SERIAL NO. ~~Divisional of~~
~~10/047,964~~

Tze-Chiang Chen et al.

10-650890

FILING ~~8-29-03~~
8/27/03

GROUP
5250 2825

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
CL	6,043,152	03/28/2000	Chang et al.			
	6,080,529	06/27/2000	Ye et al.			
	6,099,701	08/08/2000	Liu et al.			
	6,107,188	08/22/2000	Liu et al.			
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		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
CL	✓	WO 00/19523	06/06/2000	CA,CN,JP, European Patent				
	✓	JP2001015480A	01/19/2001	Japan				
	✓	JP2001053076A	02/23/2001	Japan				
	✓	JP1111843A	04/28/1989	Japan				
CL		WO 99/33102	07/01/1999	JP,KR, European Patent				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

CL	✓	Soo Geun Lee et al., "Low Dielectric Constant 3MS a-SiC:H as Cu Diffusion Barrier Layer in Cu Dual Damascene Process," Japanese Journal of Applied Physics, Part 1, Vol. 40, No. 4B, pp. 2663-2668, April 2001.
CL	✓	R.D. Goldblatt et al., "A High Performance 0.13 um Copper BEOL Technology with Low-k Dielectric," Proceedings of the IEEE 2000 International Interconnect Technology Conference, pp. 261-263, June 5-7, 2000.

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DATE CONSIDERED *7.26.04*

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Tze-Chiang Chen et al.

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*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<u>CL</u>	6,261,951 B1	07/17/2001	Buchwalter et al.			
	US 2001/0000155 A1	04/05/2001	Huang et al.			
	US 2001/0002333 A1	05/31/2001	Huang et al.			
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	US 2001/0003064 A1	06/07/2001	Ohto			
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						YES	NO

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<u>CL</u>	<input checked="" type="checkbox"/>	J. Yota et al., "Comparison Between HDP CVD and PECVD Silicon Nitride for Advanced Interconnect Applications," Proceedings of the IEEE 2000 International Interconnect Technology Conference, pp. 76-78, June 5-7, 2000.

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